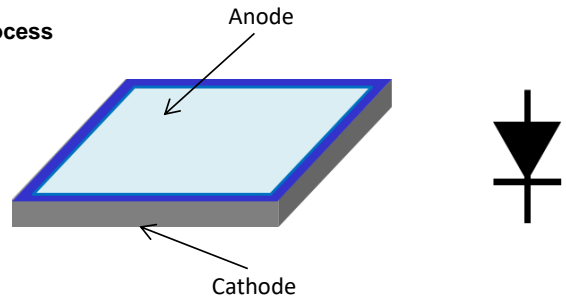


YJ Planar Schottky Barrier Diode Die Specification

200V 200A, 250mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB275H200AS-290A

Main Products Characteristics

- Average forward current: $I_{F(AV)} = 200\text{ A}$
- Maximum operating junction temperature: $T_j = 175\text{ °C}$
- ESD rating: >8KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL



Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	200 V
Average forward current	$I_{F(AV)}$	200 A
Non-repetitive peak surge current ($t_p = 8.3\text{ ms}$, halfwave, 1 cycle)	I_{FSM}	500 A
Storage temperature range	T_{stg}	-50 to +175 °C
Maximum operating junction temperature	T_j	175 °C

Static Electrical Characteristics ($T_a = 25\text{ °C}$)

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage $I_R = 1\text{ mA}$	V_{BR}	205 V	220V
Maximum forward voltage drop $I_F = 200\text{ A}$ Pulse Test: $t_p = 300\text{ }\mu\text{s}$, $\delta \leq 2\%$	V_F	0.95V	0.88V
Maximum reverse current $V_R = V_{RRM}$ Pulse Test: $t_p = 300\text{ }\mu\text{s}$, $\delta \leq 2\%$	I_R	20uA	5uA

Device Schematics and Outline Drawing

Die Thickness *	11.4 Mils
Die Size **	275 Mils
Top Metal Pad	269 Mils
Active Area	258.5 Mils
Top Metal	AL
Back Metal	Ag

Note: 1 *: Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

<p>Specification apply to die only. Actual performance may degrade when assembled.</p> <p>Yangjie Electronics does not guarantee device performance after assembly. All operating parameters must be validated for each customer application by customer's technical experts.</p> <p>Data sheet information is subjected to change without notice.</p>	<p>Recommended Storage Environment:</p> <p>Store in original container, in dessicated nitrogen, with no contamination.</p> <p>Shelf life for parts stored in above condition is 2 years.</p> <p>If the storage is done in normal atmosphere shelf life is reduced to 6 months.</p>
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